TIP131, TIP132 (NPN), TIP137 (PNP)

Darlington Complementary Silicon Power Transistors

Designed for general-purpose amplifier and low-speed switching applications.

Features

• High DC Current Gain -

$$h_{FE} = 2500 \text{ (Typ)} @ I_{C}$$

= 4.0 Adc

= 4.0 Auc

• Collector-Emitter Sustaining Voltage - @ 30 mAdc

• Low Collector-Emitter Saturation Voltage -

$$V_{CE(sat)} = 2.0 \text{ Vdc (Max)} @ I_C = 4.0 \text{ Adc}$$

= 3.0 Vdc (Max) @ $I_C = 6.0 \text{ Adc}$

- Monolithic Construction with Built-In Base-Emitter Shunt Resistors
- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	TIP131	TIP132 TIP137	Unit
	,			Vdc
Collector-Emitter Voltage	V _{CEO}	80	100	vac
Collector-Base Voltage	V_{CB}	80	100	Vdc
Emitter-Base Voltage	V _{EB}	5.0		Vdc
Collector Current - Continuous	Ic	8.0		Adc
Peak		12		
Base Current	I _B	300		mAdc
Total Power Dissipation @ T _C = 25°C	P_{D}	70		W
Total Power Dissipation @ T _A = 25°C	P_D	2.0		W
Operating and Storage Junction, Temperature Range	T _J , T _{stg}	-65 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.78	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	63.5	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

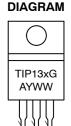


ON Semiconductor®

http://onsemi.com

DARLINGTON 8 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 80-100 VOLTS, 70 WATTS





MARKING

TIP13x = Device Code x = 1, 2, or 7

A = Assembly Location

Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping		
TIP131	TO-220	50 Units/Rail		
TIP131G	TO-220 (Pb-Free)	50 Units/Rail		
TIP132	TO-220	50 Units/Rail		
TIP132G	TO-220 (Pb-Free)	50 Units/Rail		
TIP137	TO-220	50 Units/Rail		
TIP137G	TO-220 (Pb-Free)	50 Units/Rail		

1

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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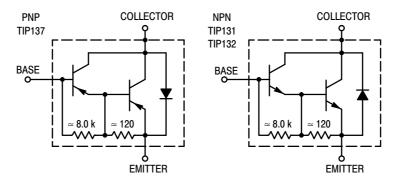


Figure 1. Darlington Circuit Schematic

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 1) (I _C = 30 mAdc, I _B = 0)	TIP131 TIP132, TIP137	V _{CEO(sus)}	80 100	- -	Vdc
Collector Cutoff Current $(V_{CE} = 40 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 50 \text{ Vdc}, I_B = 0)$	TIP131 TIP132, TIP137	I _{CEO}	- -	0.5 0.5	mAdc
Collector Cutoff Current $(V_{CB} = 80 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 100 \text{ Vdc}, I_E = 0)$	TIP131 TIP132, TIP137	I _{CBO}	- -	0.2 0.2	mAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)		I _{EBO}	-	5.0	mAdc
ON CHARACTERISTICS (Note 1)					
DC Current Gain $ (I_C = 1.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}) $ $ (I_C = 4.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}) $		h _{FE}	500 1000	_ 15000	-
Collector–Emitter Saturation Voltage ($I_C = 4.0$ Adc, $I_B = 16$ mAdc) ($I_C = 6.0$ Adc, $I_B = 30$ mAdc)		V _{CE(sat)}	- -	2.0 3.0	Vdc
Base–Emitter On Voltage (I _C = 4.0 Adc, V _{CE} = 4.0 Vdc)		V _{BE(on)}	-	2.5	Vdc

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

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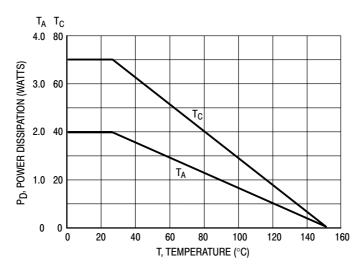


Figure 2. Power Derating

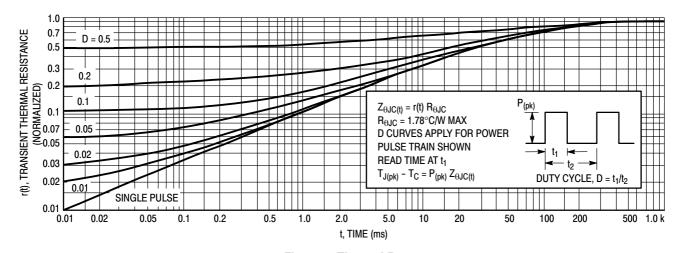


Figure 3. Thermal Response

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